Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-7 (Canceled)

8. (Original) A semiconductor device comprising a plurality of TFTs, each of the TFTs comprising:

a semiconductor layer formed on an insulating surface;

an insulating film formed on the semiconductor layer; and

a gate electrode formed on the insulating film, the gate electrode having a three-layer laminate structure,

wherein said plurality of TFTs have the same conductivity type.

9. (Original) A device according to claim 8, wherein the gate electrode comprises a material film containing mainly TaN, a material film containing mailing Al, and a material film containing mainly Ti.

10. (Original) A device according to claim 8, wherein the gate electrode comprises a material film containing mainly W, a material film containing mainly Al, and a material film containing mainly Ti.

11. (Original) A device according to claim 8, wherein said plurality of TFTs are n-channel TFTs.

12. (Original) A device according to claim 8, wherein said plurality of TFTs are p-channel TFTs.

13. (Original) A device according to claim 8, wherein TFTs formed in a driving circuit of the semiconductor device compose one of an EEMOS circuit and an EDMOS circuit.

14. (Original) A device according to claim 8, wherein the semiconductor device is a liquid crystal module of one of a transmission type and a reflection type.

15. (Original) A device according to claim 8, wherein the semiconductor device is a light emitting device having an OLED.

16. (Original) A device according to claim 8, wherein the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a car navigation system, a personal computer, a portable information terminal, and an electronic game device.

17. (Original) A method of manufacturing the steps of:

forming a semiconductor layer on an insulating surface;

forming a first insulating film on the semiconductor layer;

forming a gate electrode, a source wiring of a pixel portion, and an electrode of a terminal portion on the first insulating film;

adding an impurity element for providing an n-type to the semiconductor layer using the gate electrode as a mask to form an n-type impurity region;

etching the gate electrode to form a taper portion;

forming a second insulating film which covers the source wiring of the pixel portion and the terminal portion; and

forming a gate wiring and a source wiring of the driver circuit on the second insulating film.

18. (Original) A method according to claim 17, wherein in the step of forming the gate electrode, the source wiring of the pixel portion, and the electrode of the terminal portion, a material film containing mainly TaN, a material film containing mainly Al, and a material film containing mainly Ti are formed to be laminated, and then etched using a mask to form the gate electrode, the source wiring of the pixel portion, and the electrode of the terminal portion.

19. (Original) A method according to claim 17, wherein in the step of forming the gate electrode, the source wiring of the pixel portion, and the electrode of the terminal portion, a material film containing mainly W, a material film containing mainly Al, and a material film containing mainly Ti are formed to be laminated, and then etched using a mask to form the gate electrode, the source wiring of the pixel portion, and the electrode of the terminal portion.

20. (Original) A method according to claim 17, wherein the semiconductor device is a light emitting device having an OLED.

21. (Original) A method according to claim 17, wherein the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a car navigation system, a personal computer, a portable information terminal, and an electronic game device.